

isc Silicon PNP Power Transistor

2SB1291

DESCRIPTION

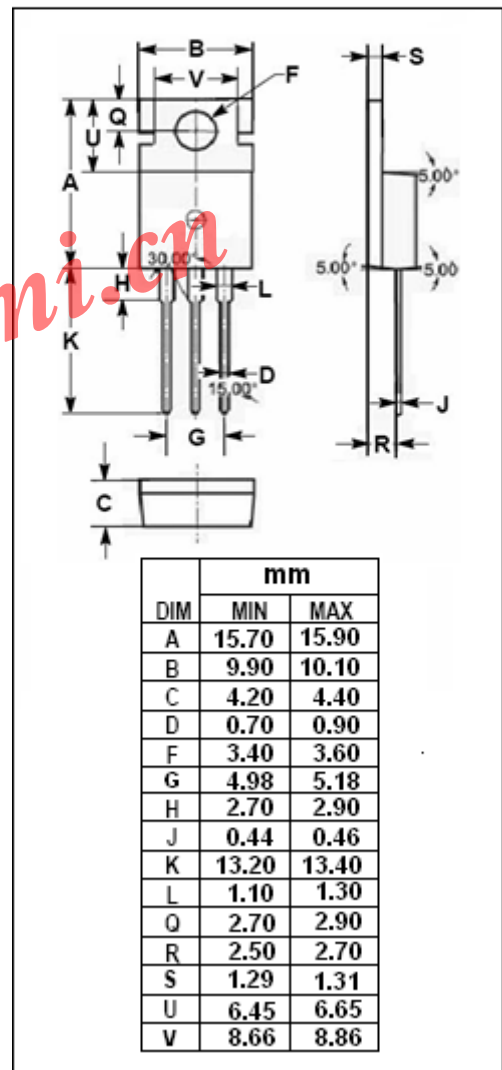
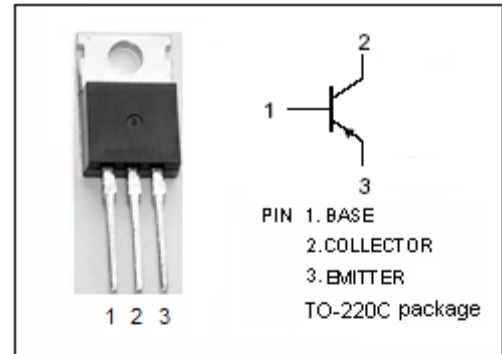
- High Collector Current:  $I_C = -5A$
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -1.5V(\text{Max}) @ I_C = -3A$
- Wide Area of Safe Operation
- Complement to Type 2SD1720

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-5	A
$I_{CM}$	Collector Current-Peak	-10	A
$P_C$	Total Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; I_B = 0$	-60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -50\ \mu\text{A}; I_E = 0$	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -50\ \mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -60\text{V}; I_E = 0$			-10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	100		320	
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1\text{MHz}$		150		pF
$f_T$	Current-Gain—Bandwidth Product	$I_E = 0.5\text{A}; V_{CE} = -5\text{V}$		12		MHz

◆  $h_{FE}$  Classifications

E	F
100-200	160-320